



P-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

- Low R_{DS(ON)}:
 - $80 \text{ m}\Omega$ @V_{GS} = -4.5V
 - 110 m Ω @V_{GS} = -2.7V
 - 130 m Ω @V_{GS} = -2.5V
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- "Green" Device (Note 4)

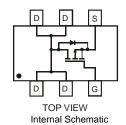
Mechanical Data

- Case: SOT-26
- Case Material Molded Plastic. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 2
- Ordering Information: See page 2
- Weight: 0.008 grams (approximate)

SOT-26







Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		V_{DSS}	-20	V
Gate-Source Voltage		V _{GSS}	±12	V
Drain Current (Note 1) Continuous	$T_A = 25$ °C $T_A = 70$ °C	I _D	-3.4 -2.7	А
Pulsed Drain Current (Note 2)		I _{DM}	-12	A
Body-Diode Continuous Current (Note 1)		Is	2.0	А

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 1)	P_{D}	1.25	W
Thermal Resistance, Junction to Ambient (Note 1); Steady-State	$R_{ heta JA}$	100	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- 1. Device mounted on 1"x1", FR-4 PC board with 2 oz. Copper and test pulse width t ≤10s.
- 2. Repetitive Rating, pulse width limited by junction temperature.
- 3. No purposefully added lead.
- 4. Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

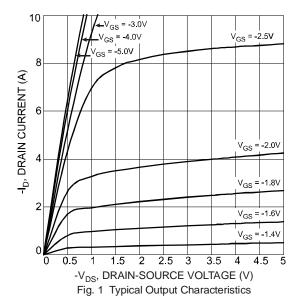


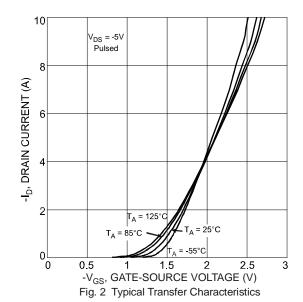
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	_	V	$I_D = -250 \mu A, V_{GS} = 0 V$
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	_	_	-1	μΑ	V _{DS} = -20V, V _{GS} = 0V
Gate-Body Leakage Current	I _{GSS}	_	_	±100	nA	$V_{DS} = 0V, V_{GS} = \pm 12V$
Gate Threshold Voltage	V _{GS(th)}	-0.6	_	-1.25	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
On State Drain Current (Note 5)	I _{D (ON)}	-15	_	_	Α	V _{GS} = -4.5V, V _{DS} = -5V
			51	80		$V_{GS} = -4.5V$, $I_D = -4.5A$
Static Drain-Source On-Resistance (Note 5)	R _{DS (ON)}	_	82	110	mΩ	$V_{GS} = -2.7V$, $I_D = -3.8A$
	, ,		94	130		$V_{GS} = -2.5V, I_D = -3.7A$
Forward Transconductance (Note 5)	g _{FS}	_	6.3	_	S	$V_{DS} = -10V$, $I_D = -4.5A$
Diode Forward Voltage (Note 5)	V_{SD}	_	0.79	-1.26	V	$I_S = -1.7A$, $V_{GS} = 0V$
Maximum Body-Diode Continuous Current (Note 1)		_	_	1.7	Α	_
DYNAMIC PARAMETERS (Note 6)						
Total Gate Charge	Qg	_	7.3	_	nC	$V_{GS} = -4.5V$, $V_{DS} = -10V$, $I_D = 4.5A$
Gate-Source Charge	Qgs	_	2.0	_	nC	$V_{GS} = -4.5V$, $V_{DS} = -10V$, $I_D = 4.5A$
Gate-Drain Charge	Q_{gd}	_	1.9	_	nC	$V_{GS} = -4.5V$, $V_{DS} = -10V$, $I_D = 4.5A$
Turn-On Delay Time	t _{D(on)}	_	12	_	ns	
Turn-On Rise Time		_	20	_	ns	$V_{DS} = -10V, V_{GS} = -4.5V,$
Turn-Off Delay Time		_	38	_	ns	$R_L = 10\Omega$, $R_G = 6\Omega$
Turn-Off Fall Time	t _f	_	41	_	ns	
Input Capacitance		_	443	_	pF	404.44
Output Capacitance		_	125	_	pF	$V_{DS} = -16V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance		_	98	_	pF] = 1.∪IVI⊓Z

Notes:

- 5. Test pulse width t = 300µs.6. Guaranteed by design. Not subject to production testing.







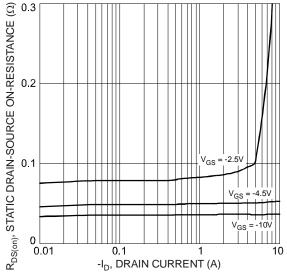


Fig. 3 On-Resistance vs. Drain Current and Gate Voltage

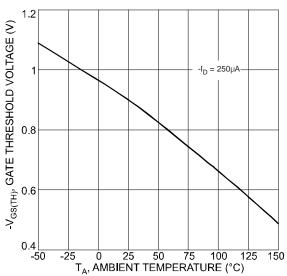


Fig. 5 Gate Threshold Voltage vs. Ambient Temperature

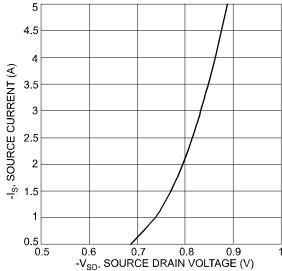


Fig. 7 Reverse Drain Current vs. Source-Drain Voltage

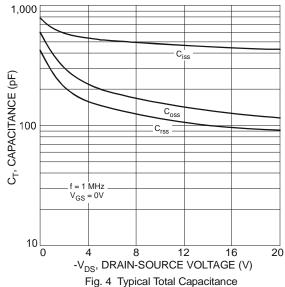


Fig. 6 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature

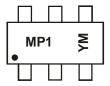


Ordering Information (Note 7)

Part Number	Case	Packaging
DMP2130LDM-7	SOT-26	3000/Tape & Reel

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

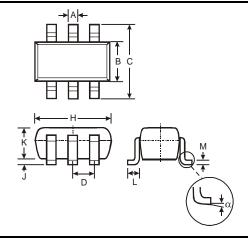


MP1 = Product Type Marking Code YM = Date Code Marking Y = Year ex: U = 2007 M = Month ex: 9 = September

Date Code Key

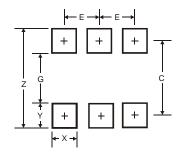
Year	20	07	20	08	20	09	20	10	20	11	20	12
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Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

Package Outline Dimensions



SOT-26						
Dim	Min	Max	Тур			
Α	0.35	0.50	0.38			
В	1.50	1.70	1.60			
С	2.70	3.00	2.80			
D	_		0.95			
Н	2.90	3.10	3.00			
J	0.013	0.10	0.05			
K	1.00	1.30	1.10			
L	0.35	0.55	0.40			
М	0.10	0.20	0.15			
α	0°	8°				
All Dimensions in mm						

Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Υ	0.80
С	2.40
Е	0.95

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